Sample Introduction System Allows for Analysis of SiC Wafers up to 4” in Diameter

Nitrogen Analysis.
A N detection limit of ~ 2e16 atoms/cc can be achieved after ~ 2 hours of pumping.

Excellent load to load reproducibility.
Load to load reproducibility was tested by introducing the sample multiple times.
SiC 4-inch Whole Wafer Analysis

SIMS profile of Al and N from a 2" SiC wafer. The Al profile was acquired using oxygen beam sputtering, and N profile was acquired using Cs beam sputtering. The whole wafer capability provides doping concentration and thickness of each epi layer without breaking the wafer.